Code No.: EC301PC

[Time: 3 Hours]

R20 H.T.No. R

[Max. Marks: 70]

## CMR ENGINEERING COLLEGE: : HYDERABAD UGC AUTONOMOUS

## II-B.TECH-I-Semester End Examinations (Supply) - December - 2024 ELECTRONIC DEVICES AND CIRCUITS

(ECE)

	[Time:	3 Hours]	
		his question paper contains two parts A and B.  art A is compulsory which carries 20 marks. Answer all questions in Part A.  art A is compulsory which carries 20 marks. Answer all question from each unit. Each question	
Part A is compulsory which carries 20 marks. Answer an question from each unit. Each question Part B consists of 5 Units. Answer any one full question from each unit. Each question			
	P	arries 10 marks and may have a, b, c as sub questions.	
	C	arries 10 marks and may have a, o, e as sae que	
		PART-A  (20 Ms)	arks)
		with the second	[2M]
	1. a)	Define diffusion and transition capacitance.	[2M]
	b)	List out the different types of clipper circuits.	[2M]
	()	Draw the symbols of NPN and PNP transistor.	[2M]
	d)	Define rise time and fall time for a transistor.	[2M]
	e)	Write the differences between BJT and FE1.	[2M]
	f)	List out the applications of photo diode.	[2M]
	g)	Define an amplifier? List out the applications of amplifier.	[2M]
	h)	What is the need of coupling and bypass capacitors in CE amplifier?	[2M]
	i)	Draw the circuit diagram of common source JFET amplifier.	[2M]
	j)	Write the classification of MOSFET along with their symbols.	
		$\mathbf{p}_{\bullet}\mathbf{p}_{T}\mathbf{p}_{T} \tag{50 N}$	Aarks)
		Explain PN junction diode in forward and reverse bias condition along with	[7M]
	2.a)	Explain PN junction diode in forward and reverse olds condition	
		V-I characteristics.	[3M]
	b)	Explain about load line analysis.  OR	
		Construct and explain the operation of half wave rectifier and derive the equation for	[10M]
	3.	Construct and explain the operation of half wave rectifier and deriver	
		ripple factor and efficiency.	
		Explain the circuit for a common base configuration with their input and output	[10M]
	4.	Explain the circuit for a common base comiguration	
		characteristics.	
		OR	[10M]
	5.	Explain in detail about self bias and derive its stability factor.	
		2. 1.1 See Aprigms in a Zener diode? Explain the reverse	[10M]
	6.	What are the types of breakdown mechanisms in a Zener diode? Explain the reverse	
		bias characteristics of Zener diode.  OR	
		Explain the construction and working principle of operation for N-channel JFET with	[10M]
	7.	Explain the construction and working principle of operation for 1.	
		its characteristics.	
		- The far CE CR & CC configurations.	[10M]
	8.	Draw the BJT hybrid models for CE, CB & CC configurations.  OR	
		Draw the circuit diagram of a collector to base bias circuit of a CE amplifier and	[10M]
	9.	Draw the circuit diagram of a conector to base one	
		derive the expression for stability factor.	
		Explain the operation of Enhancement mode MOSFET in detail along with its	[10M]
	10.	Explain the operation of Editation in Explain	
		characteristics. OR	F4 03 53
		Draw the circuit diagram of CS amplifier and explain its working operation.	[10M]
	11.	Draw the circuit diagram of CS difficult and T	